



CST80P04 P-Ch 40V Fast Switching MOSFETs

- 100% EAS Guaranteed
- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

CST80P04 Product Summary



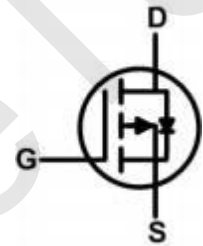
BVDSS	RDSON	ID
-40V	6.4mΩ	-80A

CST80P04 Description

The CST80P04 is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The CST80P04 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

CST80P04 TO252 Pin Configuration



CST80P04 Absolute Maximum Ratings (T_A = 25°C, unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	-40	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current	I _D	T _C =25°C	-80
		T _C =100°C	-50.6
Pulsed Drain Current ¹	I _{DM}	-320	A
Single Pulse Avalanche Energy ²	EAS	101.25	mJ
Total Power Dissipation	P _D	81.16	W
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to 150	°C

CST80P04 Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction-to-Ambient ³	R _{θJA}	54	°C/W
Thermal Resistance from Junction-to-Case	R _{θJC}	1.54	°C/W



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CST80P04 Electrical Characteristics($T_J = 25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Static Characteristics							
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-40	-	-	V	
Gate-body Leakage current	I_{gss}	$V_{DS} = 0V, V_{GS} = \pm 20V$	-	-	± 100	nA	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -40V, V_{GS} = 0V$	$T_J = 25^\circ\text{C}$	-	-	-1	pA
			$T_J = 100^\circ\text{C}$	-	-	-100	
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1.0	-1.6	-2.5	V	
Drain-Source on-Resistance ⁴	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -20A$	-	6.4	8.2	m Ω	
		$V_{GS} = -4.5V, I_D = -15A$	-	8.2	11		
Forward Transconductance ⁴	g_{fs}	$V_{DS} = -10V, I_D = -20A$	-	104	-	S	
Dynamic Characteristics⁵							
Input Capacitance	C_{iss}	$V_{DS} = -20V, V_{GS} = 0V, f = 1MHz$	-	5295	-	pF	
Output Capacitance	C_{oss}		-	430	-		
Reverse Transfer Capacitance	C_{rss}		-	385	-		
Gate Resistance	R_g	$f = 1MHz$	-	4.3	-	Q	
Switching Characteristics⁵							
Total Gate Charge	Q_g	$V_{GS} = -10V, V_{DS} = -20V, I_D = -20A$	-	110	-	nC	
Gate-Source Charge	Q_{gs}		-	12.5	-		
Gate-Drain Charge	Q_{gd}		-	23	-		
Turn-on Delay Time	$t_{d(on)}$	$V_{GS} = -10V, V_{DD} = -20V, R_G = 3\Omega, I_D = -20A$	-	16.8	-	ns	
Rise Time	t_r		-	10	-		
Turn-off Delay Time	$t_{d(off)}$		-	65	-		
Fall Time	t_f		-	17	-		
Body Diode Reverse Recovery Time	t_{rr}	$I_F = -20A, di/dt = 100A/\mu s$	-	42	-	ns	
Body Diode Reverse Recovery Charge	Q_{rr}		-	29	-	nC	
Drain-Source Body Diode Characteristics							
Diode Forward Voltage ⁴	V_{SD}	$I_S = -20A, V_{GS} = 0V$	-	-	-1.2	V	
Continuous Source Current	I_S	$T_C = 25^\circ\text{C}$	-	-	-80	A	

Notes:

1. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)} = 150^\circ\text{C}$.
2. The EAS data shows Max. rating . The test condition is $V_{DD} = -30V, V_{GS} = -10V, L = 0.1mH, I_{AS} = -45A$.
3. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
5. This value is guaranteed by design hence it is not included in the production test.



CST80P04 Typical Characteristics

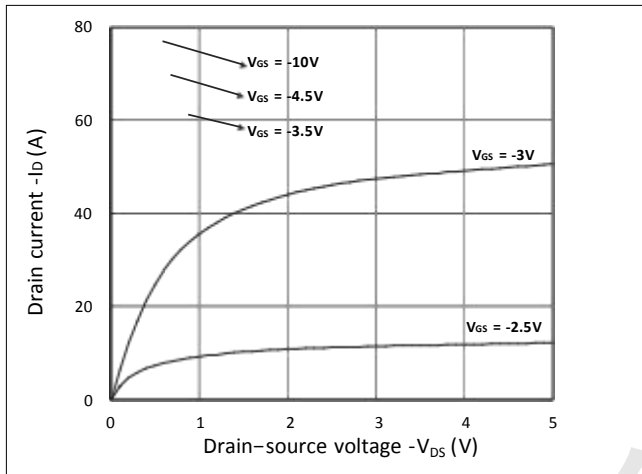


Figure 1. Output Characteristics

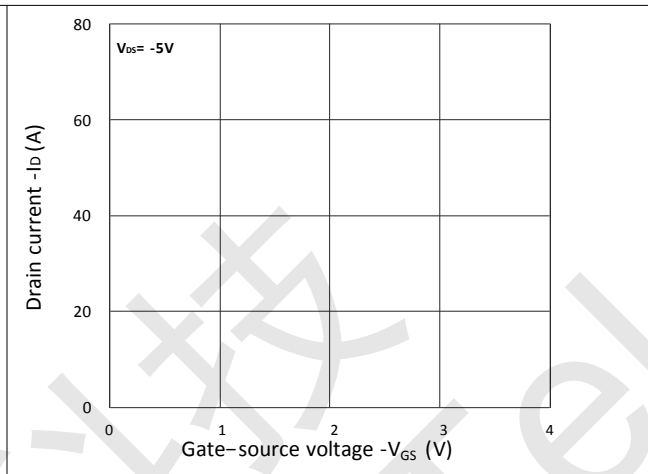


Figure 2. Transfer Characteristics

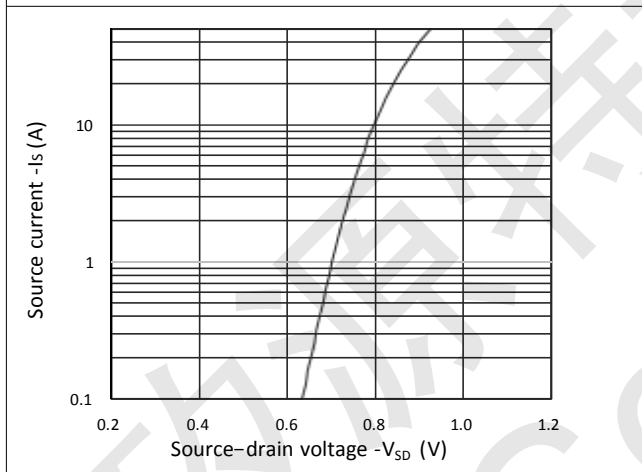


Figure 3. Forward Characteristics of Reverse

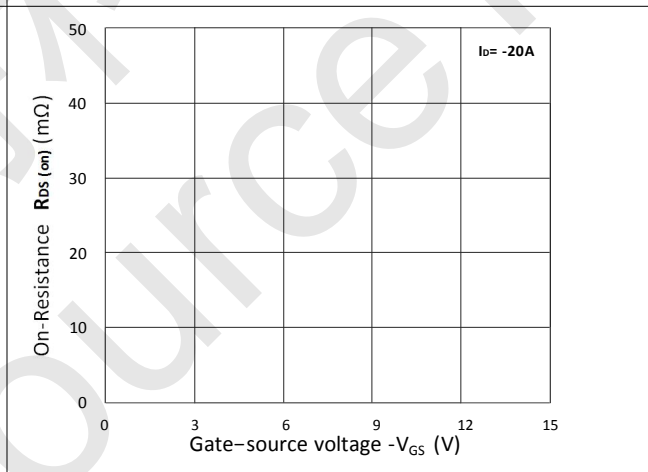


Figure 4. $R_{DS(ON)}$ vs . V_{GS}

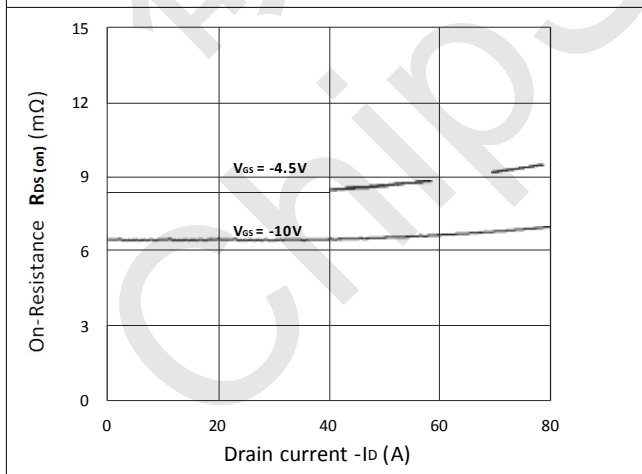


Figure 5. $R_{DS(ON)}$ vs . I_D

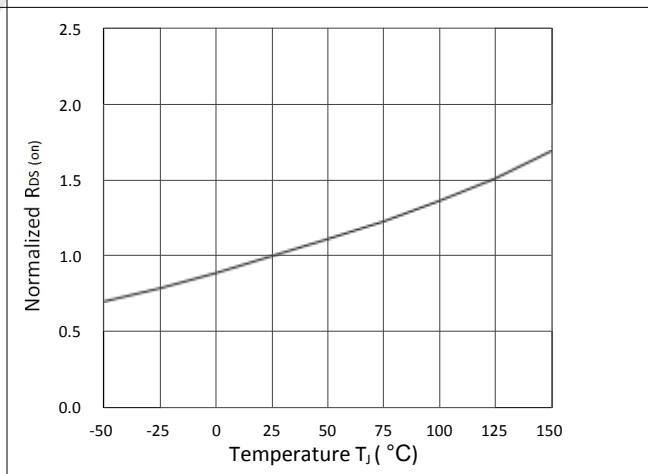


Figure 6. Normalized $R_{DS(on)}$ vs . Temperature



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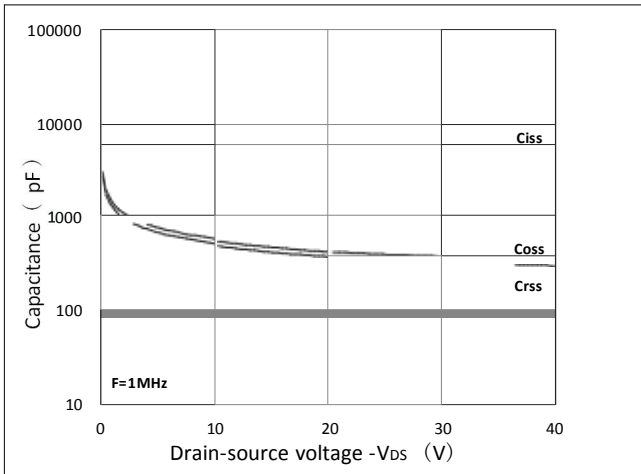


Figure 7. Capacitance Characteristics

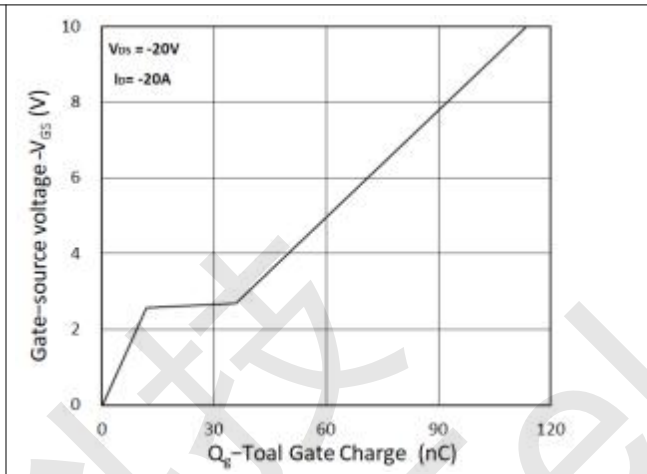


Figure 8. Gate Charge Characteristics

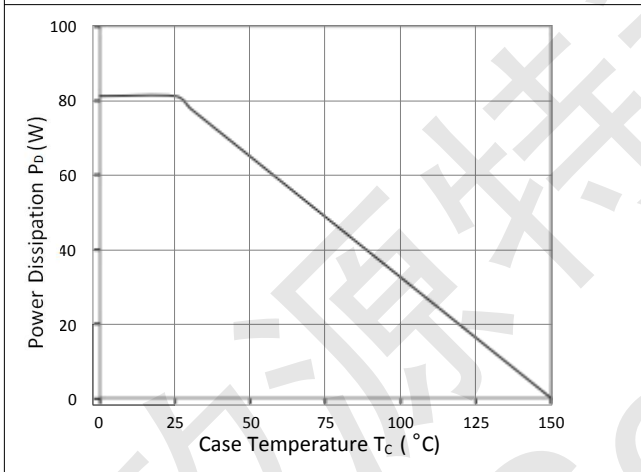


Figure 9. Power Dissipation

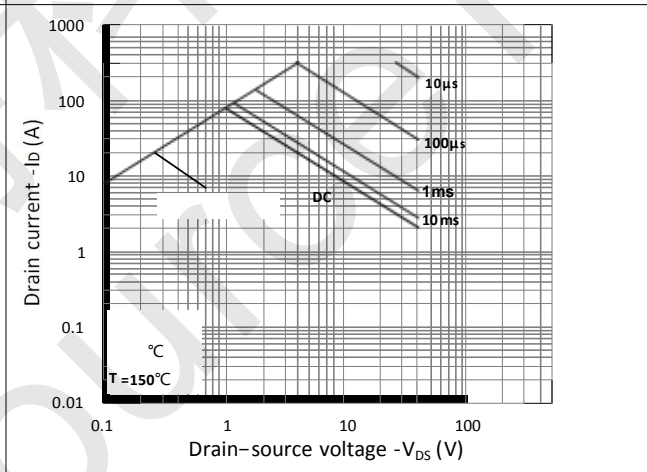


Figure 10. Safe Operating Area

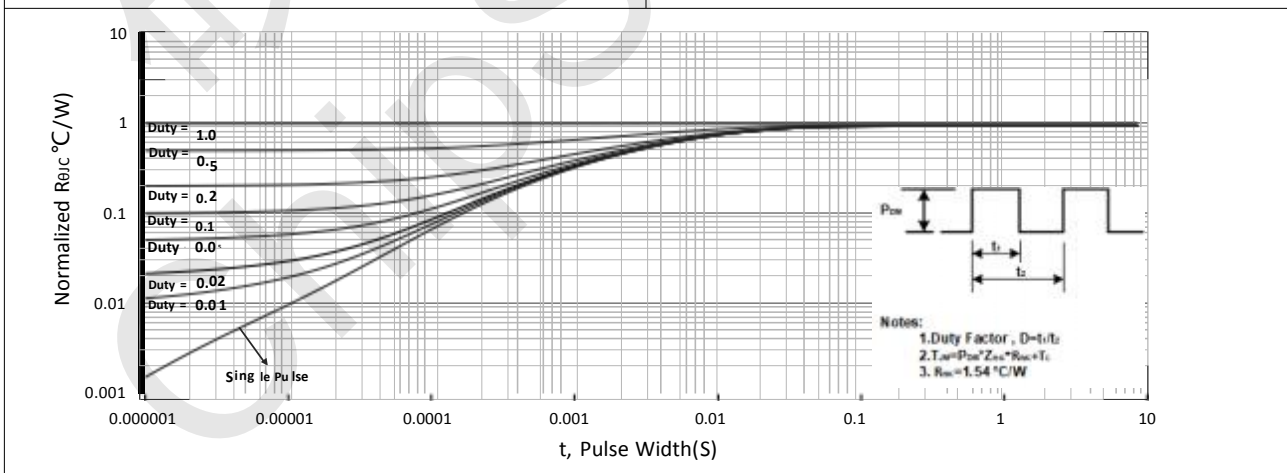


Figure 11. Normalized Maximum Transient Thermal Impedance



CST80P04 Test Circuit

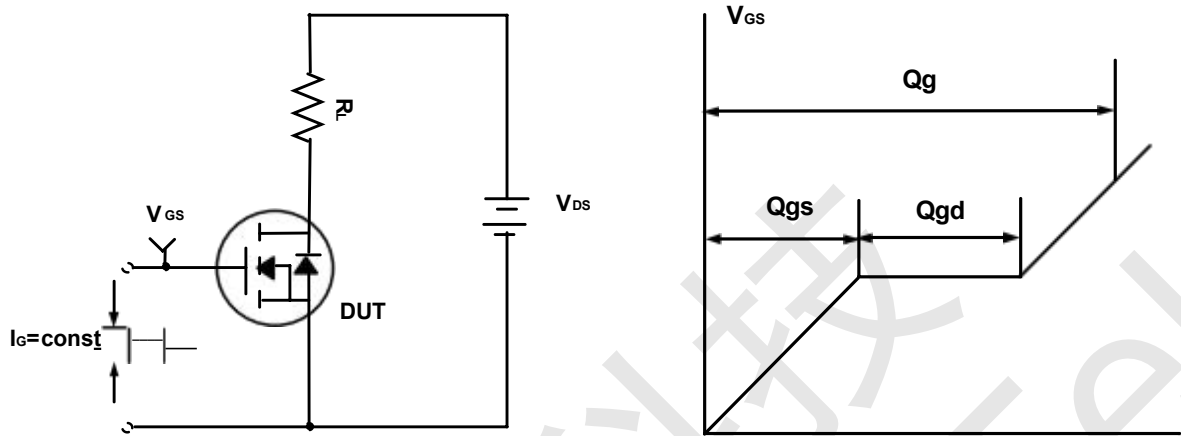


Figure A. Gate Charge Test Circuit & Waveforms

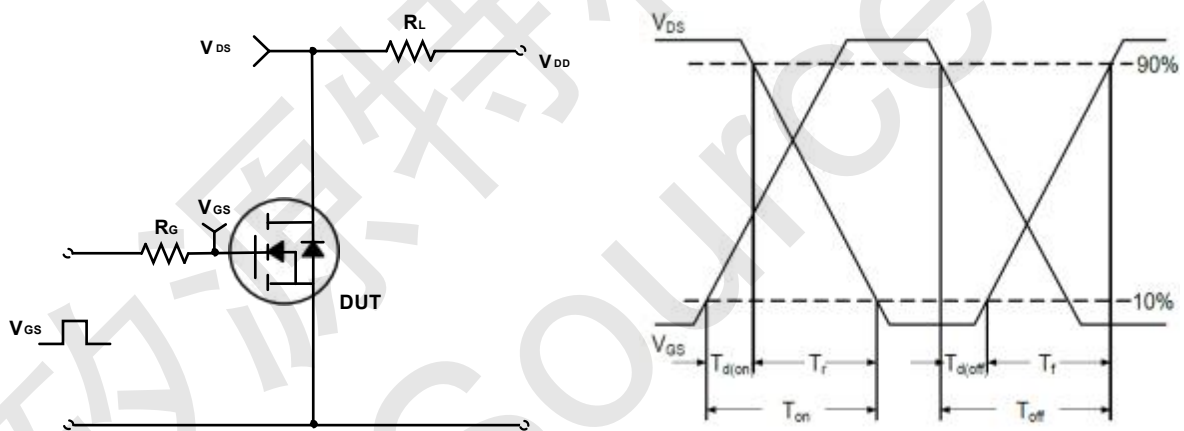


Figure B. Switching Test Circuit & Waveforms

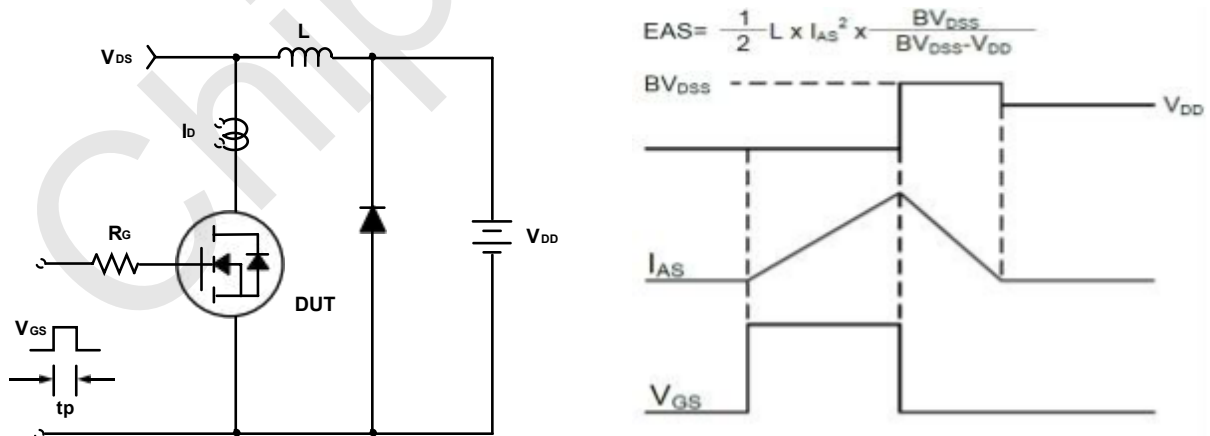
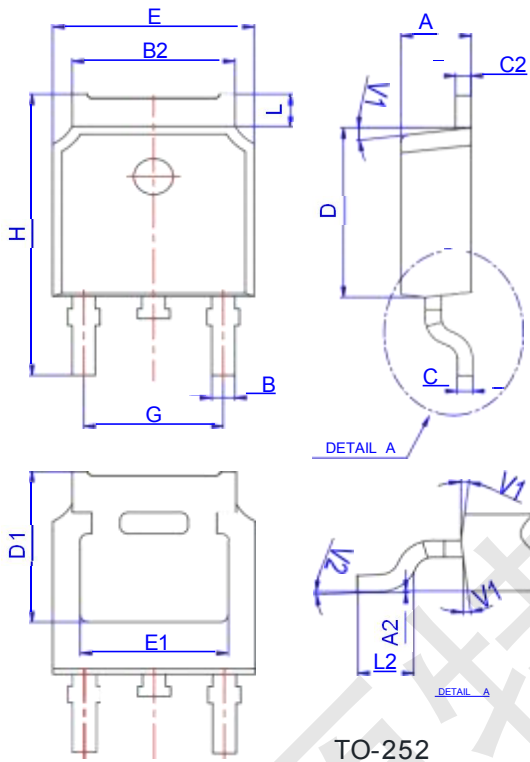


Figure C. Unclamped Inductive Switching Circuit & Waveforms



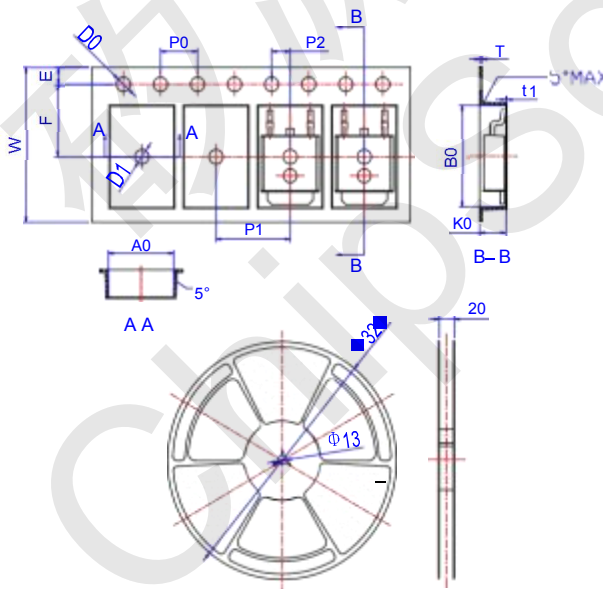
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CST80P04 Package Mechanical Data-TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°		7°		
V2	0°		6°	0°		6°

CST80P04 Reel Specification-TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583